

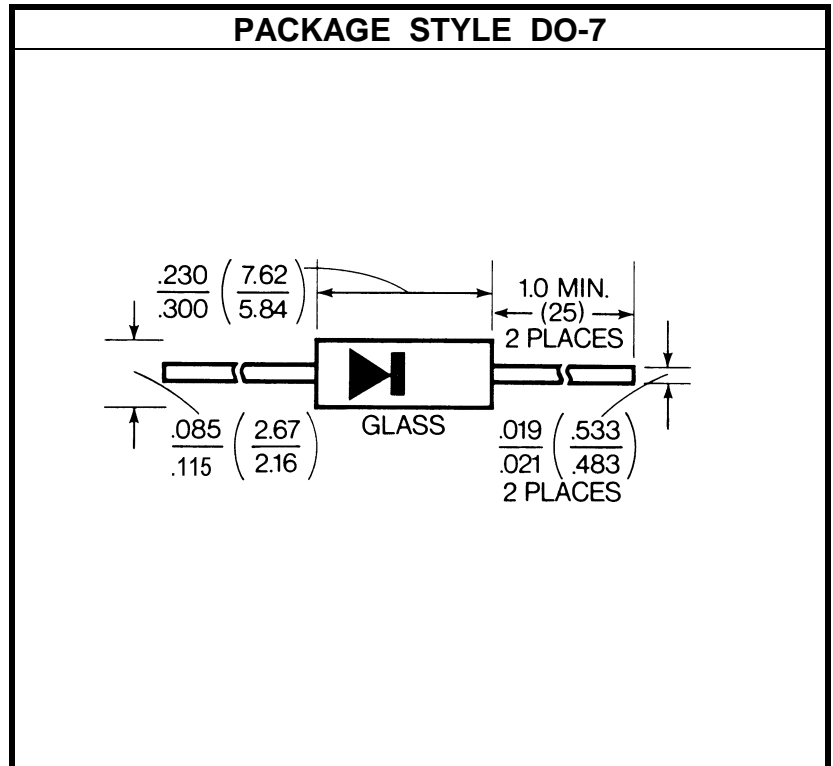
ABRUPT VARACTOR DIODE

DESCRIPTION:

The **ASI 1N5709B** is an Abrupt Varactor Diode, designed for general purpose applications.

MAXIMUM RATINGS

I_R	20 nA
V_R	70 V
P_{DISS}	400 mW @ T _A = 25 °C
T_J	-65 °C to +175 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	250 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V_{BR}	I _R = 10 μA	65			V
I_R	V _R = 60 V			20	nA
	T _A = 150 °C			20	μA
C_T	V _R = 4.0 V	f = 1.0 MHz	77.9	86.1	pF
C_{T4}/C_{T60}	V _R = 4.0 V/V _R = 60 V	f = 1.0 MHz	3.2	3.4	--
Q	V _R = 4.0 V	f = 50 MHz	150		--